

STTH30R02DJF

Ultrafast recovery diode high efficiency

Datasheet - production data

Features

- Suited for DC/DC converts
- Low losses
- High T_J
- High surge current capability
- High energy avalanche capability
- 1 mm package thickness
- ECOPACK[®]2 compliant component

Description

High performance diode suited for high frequency DC to DC converters. Packaged in PowerFLAT™ 5x6, this device is intended for use in low voltage high frequency inverters.

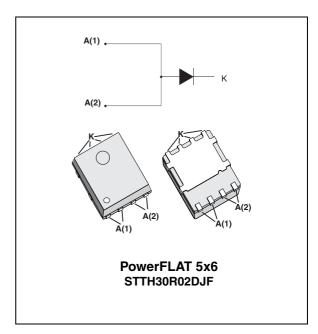


Table 1. Device summary

Symbol	Value
I _{F(AV)}	30 A
V _{RRM}	200 V
T _j	175 °C
V _F (typ)	0.8 V
t _{rr} (typ)	27 ns

TM: PowerFLAT is a trademark of STMicroelectronics

Characteristics STTH30R02DJF

1 Characteristics

Table 2. Absolute ratings (limiting values with anode terminals short-circuited)

Symbol	Parameter	Value	Unit	
V_{RRM}	Repetitive peak reverse voltage	200	V	
I _{F(RMS)}	Forward rms current	45	Α	
I _{F(AV)}	Average forward current $ T_{c} = 105 ^{\circ}\text{C} $ $ \delta = 0.5 $		30	Α
I _{FSM}	Surge non repetitive forward current $t_p = 10 \text{ ms}$ sinusoidal		300	Α
T _{stg}	Storage temperature range		-65 to + 175	°C
Tj	Maximum operating junction temperatu	175	°C	

Table 3. Thermal parameter

Symbol	Parameter	Maximum	Unit
R _{th(j-c)}	Junction to case	2.0	°C/W

Table 4. Static electrical characteristics (anode terminals short-circuited)

Symbol	Parameter	Test conditions		Min.	Тур	Max.	Unit
I _B ⁽¹⁾	Reverse leakage current	T _j = 25 °C	V = 200V			10	^
'R`´	IR. A neverse leakage current	T _j = 125 °C	$V_R = 200V$		10	100	μΑ
V _E ⁽²⁾	Forward voltage drop	T _j = 25 °C	I - 30 A		1	1.15	V
V _F ⁽²⁾ Forward voltage drop	T _j = 150 °C	$ I_F = 30 \text{ A}$		0.80	0.95	V	

^{1.} Pulse test: $t_p = 5 \text{ ms}, \delta < 2\%$

To evaluate the maximum conduction losses use the following equation:

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$$P = 0.77 \text{ x I}_{F(AV)} + 0.006 \text{ I}_{F}^{2}_{(RMS)}$$

^{2.} Pulse test: t_p = 380 μ s, δ < 2%

STTH30R02DJF Characteristics

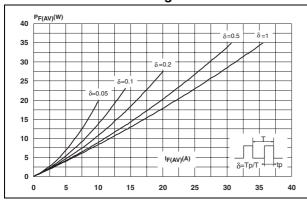
Table 5. Recovery characteristics

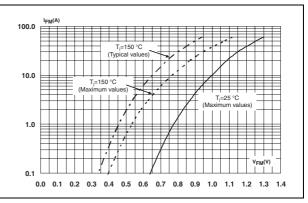
Symbol	Parameter	Test conditions		Min.	Тур	Max.	Unit
	Payorsa rasayary tima		$I_F = 1 \text{ A}$ $V_r = 30 \text{ V}$ $dI_F/dt = 100 \text{ A/}\mu\text{s}$		27	35	20
^L rr	t _{rr} Reverse recovery time		$I_F = 1 \text{ A}$ $V_r = 30 \text{ V}$ $dI_F/dt = 50 \text{ A/}\mu\text{s}$		38	50	ns
I _{RM}	Reverse recovery current		I - 20 A		6.0	8.0	Α
S _{factor}	Reverse recovery softness factor	T _j = 125 °C	$I_F = 30 \text{ A},$ $dI_F/dt = -200 \text{ A/}\mu\text{s},$ $V_{CC} = 160 \text{ V}$		0.3		-
Q _{rr}	Reverse recovery charges				140		nC

Table 6. Turn-on switching characteristics

Symbol	Parameter	Test conditions		Min.	Тур	Max.	Unit
t _{fr}	Forward recovery time		I _F = 30 A			300	ns
V _{FP}	Forward recovery voltage	T _j = 25 °C	$dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_{FR} = 1.3 \text{ V}$		2.3	3.5	V

Figure 1. Average forward power dissipation Figure 2. Forward voltage drop versus versus average forward current forward current

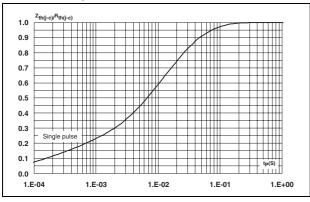




Characteristics STTH30R02DJF

Figure 3. Relative variation of thermal impedance junction to case versus pulse duration

Figure 4. Peak reverse recovery current versus dl_F/dt (typical values)



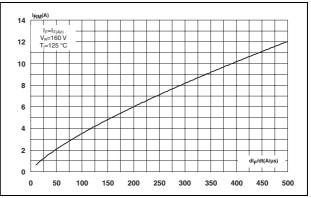
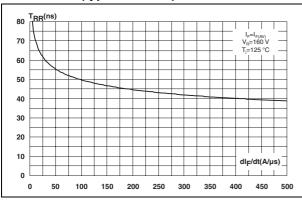


Figure 5. Reverse recovery time versus dI_F/dt Figure 6. Reverse recovery charges versus dI_F/dt (typical values)



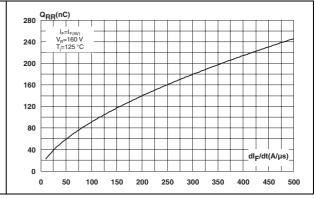
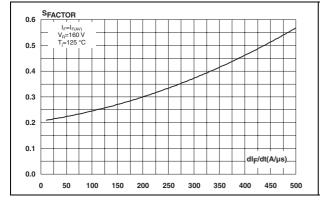
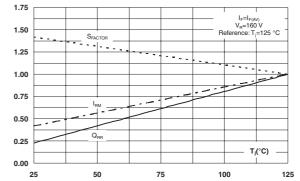


Figure 7. Softness factor versus dl_F/dt (typical values)

Figure 8. Relative variations of dynamic parameters versus junction temperature





STTH30R02DJF Characteristics

Figure 9. Transient peak forward voltage versus dl_E/dt (typical values)

 $V_{FP}(V)$

I_F=I_{F(AV)} T_j=125 °C

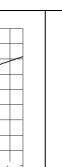


Figure 10. Forward recovery time versus dl_F/dt (typical values)

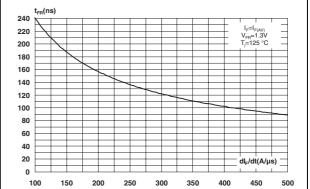


Figure 11. Junction capacitance versus reverse voltage applied (typical values)

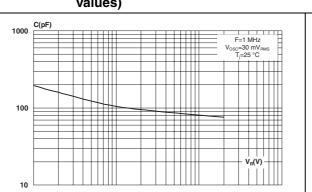
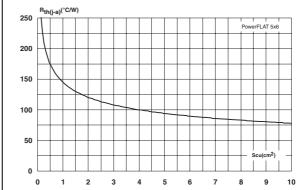


Figure 12. Thermal resistance junction to ambient versus copper surface under tab



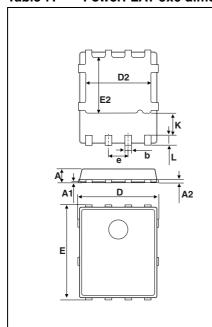
Package information STTH30R02DJF

2 Package information

- Epoxy meets UL94, V0
- Cooling method: by conduction (C)

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

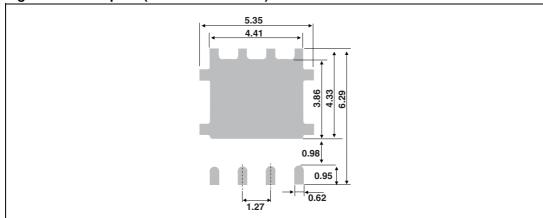
Table 7. PowerFLAT 5x6 dimensions



	Dimensions							
Ref.	Millimeter		Millimeters		Inches			
	Min.	Тур.	Max.	Min.	Тур.	Max.		
Α	0.80		1.00	0.031		0.039		
A1	0.02		0.05	0.001		0.002		
A2		0.25			0.010			
b	0.30		0.50	0.012		0.020		
D		5.20			0.205			
D2	4.11		4.31	0.162		0.170		
е		1.27			0.050			
Е		6.15			0.242			
E2	3.50		3.70	0.138		0.146		
L	0.50		0.80	0.020		0.031		
K	1.275		1.575	0.050		0.062		

Figure 13. Footprint (dimensions in mm)

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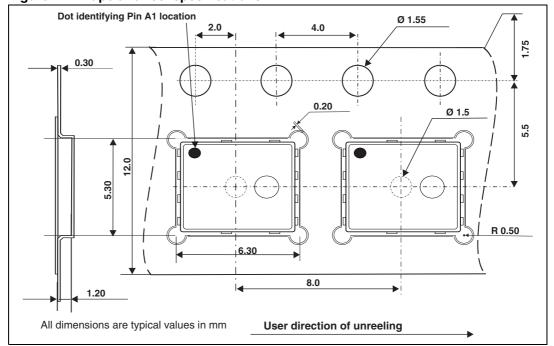


Figure 14. Tape and reel specifications

Ordering information STTH30R02DJF

3 Ordering information

Table 8. Other information

Order code	Marking	Package	Weight	Base qty	Delivery mode
STTH30R02DJF-TR	TH30R 02	PowerFLAT 5x6	0.095 g	3000	Tape and Reel

4 Revision history

Table 9. Document revision history

Date	Revision	Changes
16-Mar-2012	1	First issue.

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